

Supporting Information

Engineering interface-mediated heterojunction in MOF-derived C-In₂O₃ microrods and CdS nanoclusters for enhanced photocatalytic H₂O₂ production

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Experimental Procedure

Materials

Indium (III) nitrate hydrate ($\text{In}(\text{NO}_3)_3 \cdot x\text{H}_2\text{O}$, A.R., Aladdin), N, N-dimethylformamide (DMF, A.R., Aladdin), terephthalic acid (H_2BDC , A.R., Aladdin), Cadmium acetate ($(\text{CH}_3\text{COO})_2\text{Cd}$, A.R., Aladdin), Sodium sulfide ($\text{Na}_2\text{S} \cdot 9\text{H}_2\text{O}$, A.R., Aladdin), Ethanol anhydrous ($\text{CH}_3\text{CH}_2\text{OH}$, 99.7%, Macklin), potash iodide (KI, A.R., Aladdin), Potassium acid phthalate ($\text{C}_8\text{H}_5\text{O}_4\text{K}$, AR, Macklin), Hydrogen peroxide (30%, AR, XILONG SCIENTIFIC), deionized water (Millipore, 18.2 $\text{M}\Omega$ cm). The above chemicals were used directly and no further purification was carried out.

Characterization

Field emission scanning electron microscopy (FESEM) (Hitachi, Japan) transmission electron microscopy (TEM), and high-resolution transmission electron microscopy (HRTEM) using the JEOL JEM-F200 (Japan) were hired to observe the microstructure and morphology of the samples. X-ray power diffraction (XRD) patterns were obtained using the Bruker D8 Advance instrument from Germany with Cu K α radiation ($\lambda = 1.5406 \text{ \AA}$) to determine the crystal structures. X-ray photoelectron spectroscopy (XPS) was conducted using the Thermo Fisher Scientific ESCALAB 250Xi instrument from America to analyze the surface species and chemical states. Diffuse reflectance absorption spectra were measured on a Hitachi UV-3900 UV-visible spectrophotometer with an integrated sphere attachment, employing BaSO₄ as the reflectance standard. The specific surface area of the materials was calculated using the adsorption data in the pressure range of $P/P_0 = 0 - 1$ by the Brunauer-Emmett-Teller (BET) model. Pore size distribution was obtained by the Barrett-Joyner-Halenda (BJH) model using the adsorption branch of the isotherm. The room temperature electron paramagnetic resonance (EPR) spectra of the samples were measured by Bruker EMXplus-6/1. Photoluminescence (PL) spectra were measured on Edinburgh FLS1000 fluorescence spectrometer with an excitation wavelength of 350 nm. Time-resolved photoluminescence (TRPL) spectra were collected on Edinburgh FLS1000 fluorescence spectrometer with an excitation wavelength of 470 nm.

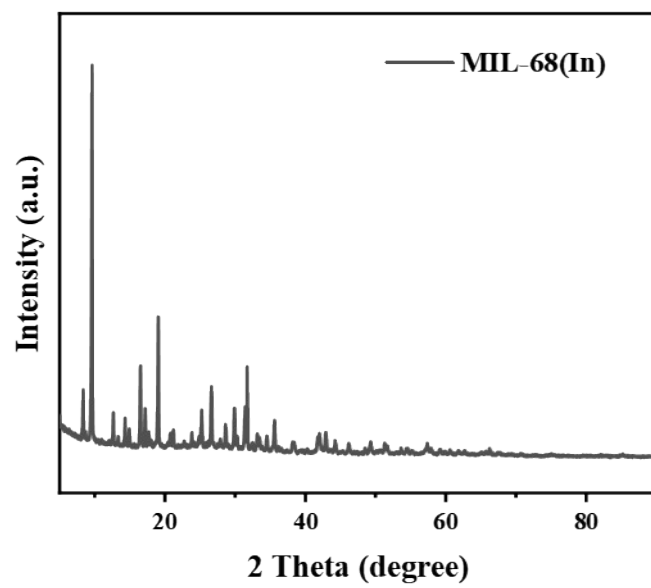


Fig. S1 XRD spectra of as-prepared MIL-68(In).

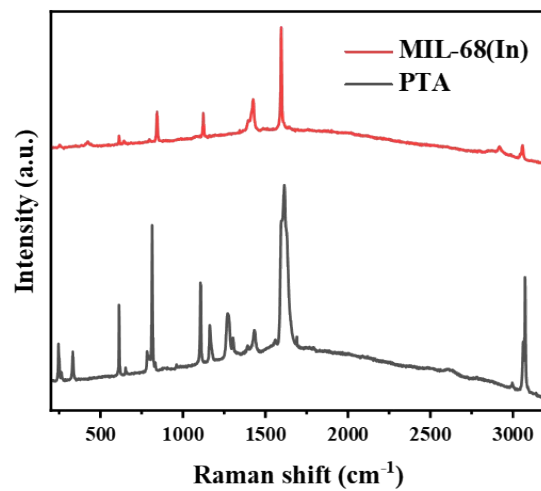


Fig. S2 Raman spectra of as-prepared MIL-68(In) and PTA.

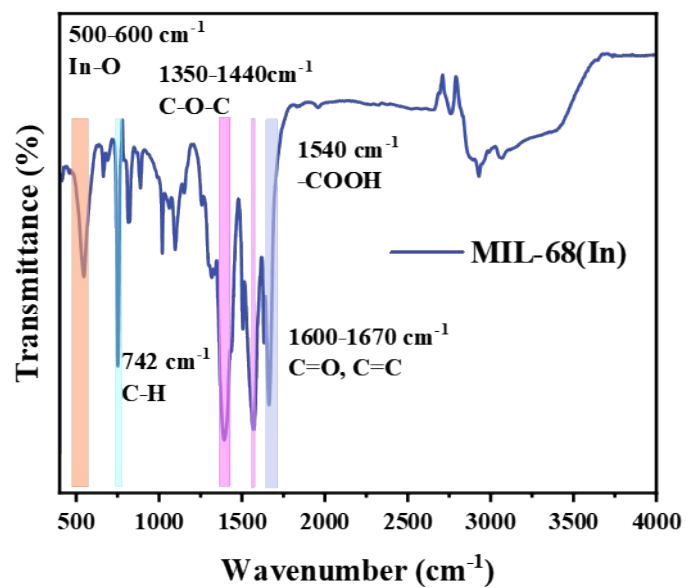


Fig. S3 FT-IR spectra of as-prepared MIL-68(In).

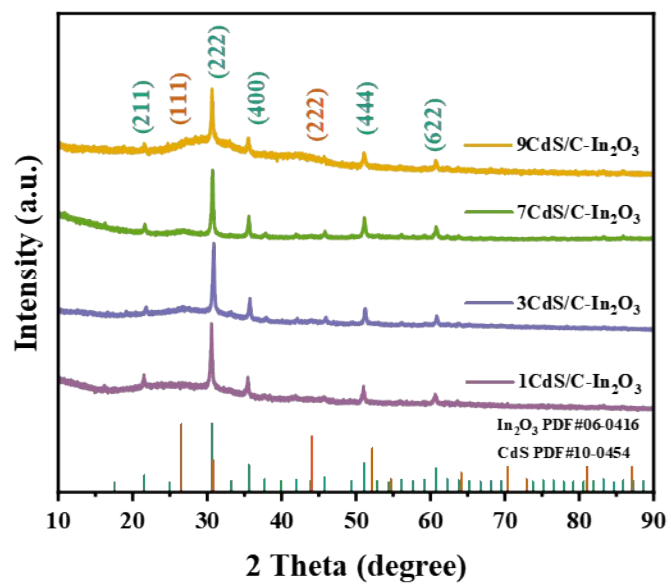


Fig. S4 XRD patterns of as-prepared CdS/C-In₂O₃

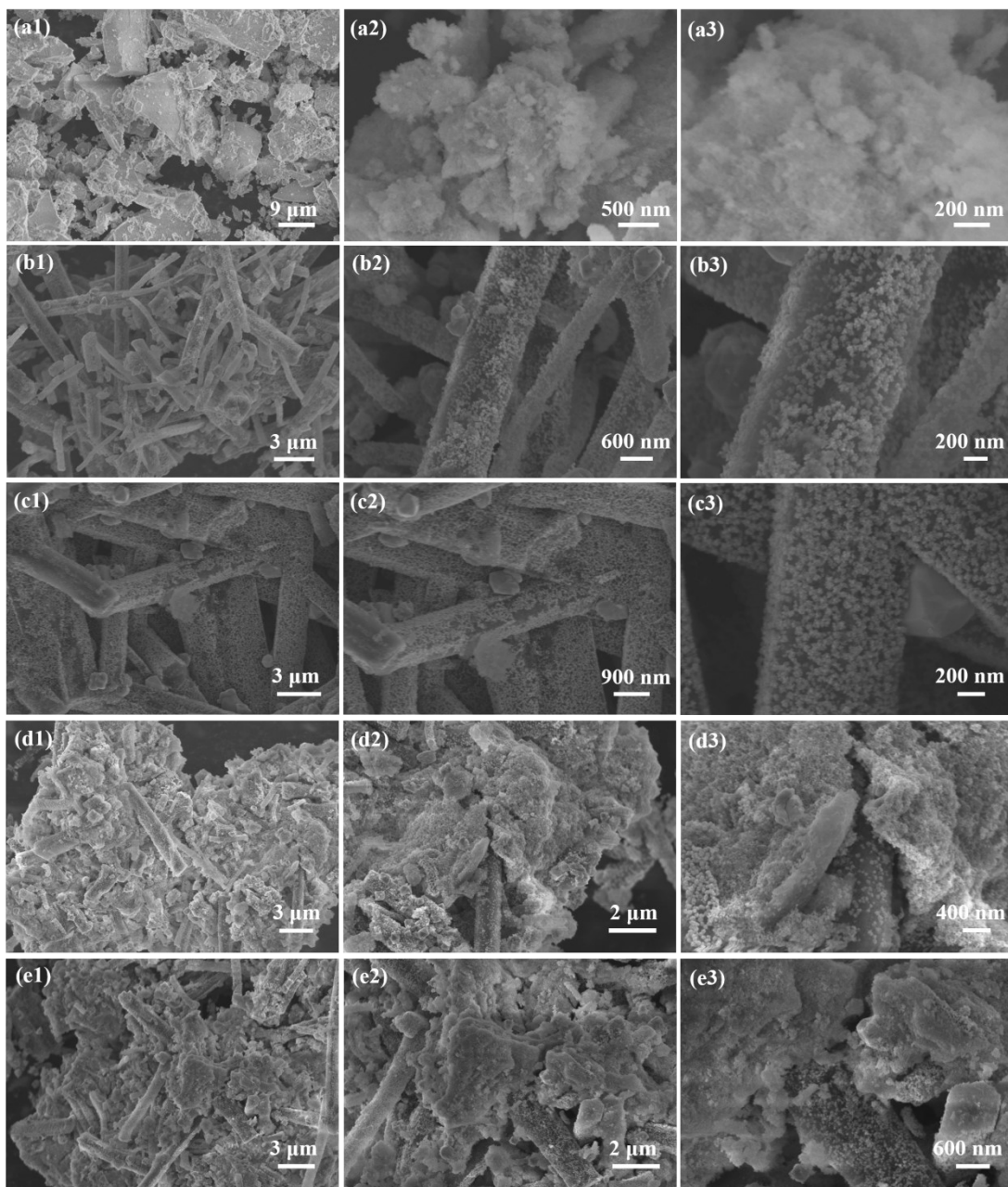


Fig. S5 Typical SEM images of (a) CdS, (b) 1CdS/C-In₂O₃, (c) 3CdS/C-In₂O₃, (d) 7CdS/C-In₂O₃, (e) 9CdS/C-In₂O₃.

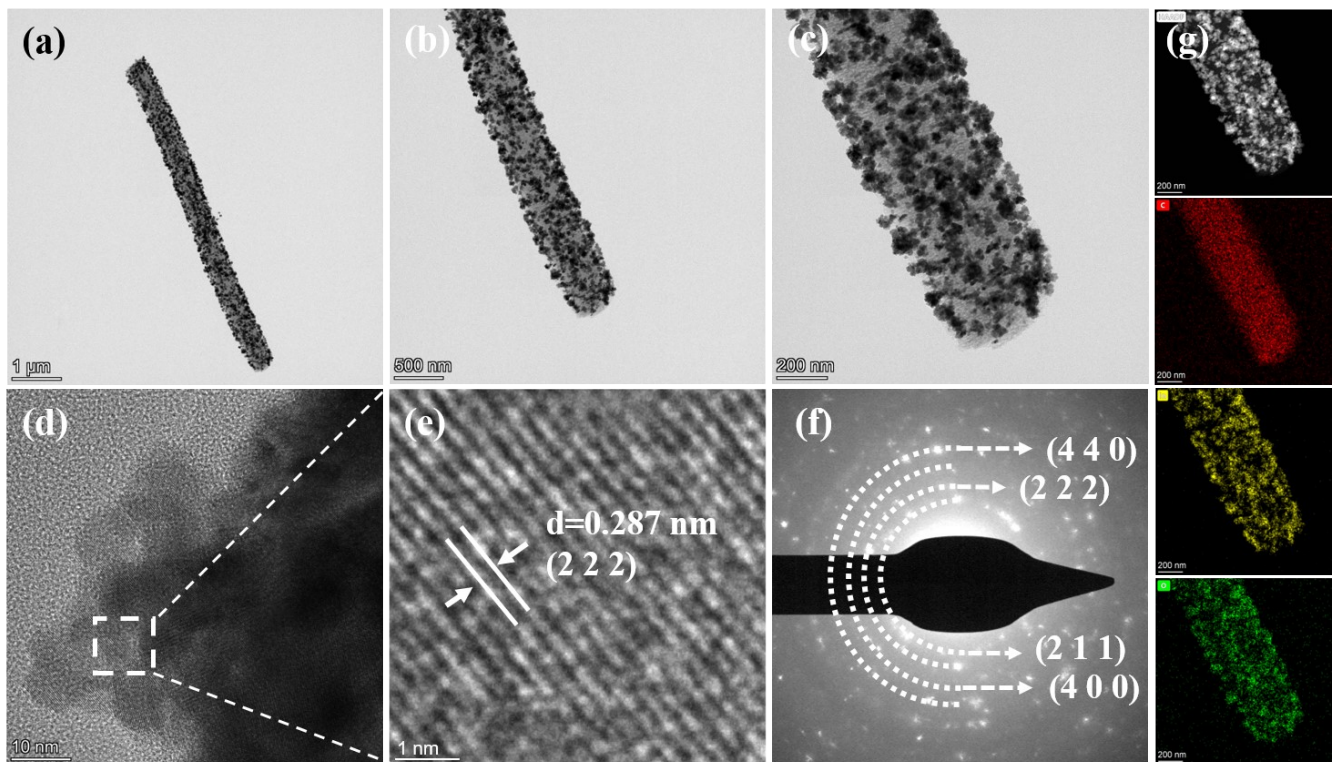


Fig. S6 (a-d) Typical TEM images of C-In₂O₃. (e) Typical HRTEM images recorded from the marked area in (d). Corresponding (f) SAED spectrum of C-In₂O₃. (g) Elemental mappings corresponding to the selected area of C-In₂O₃.

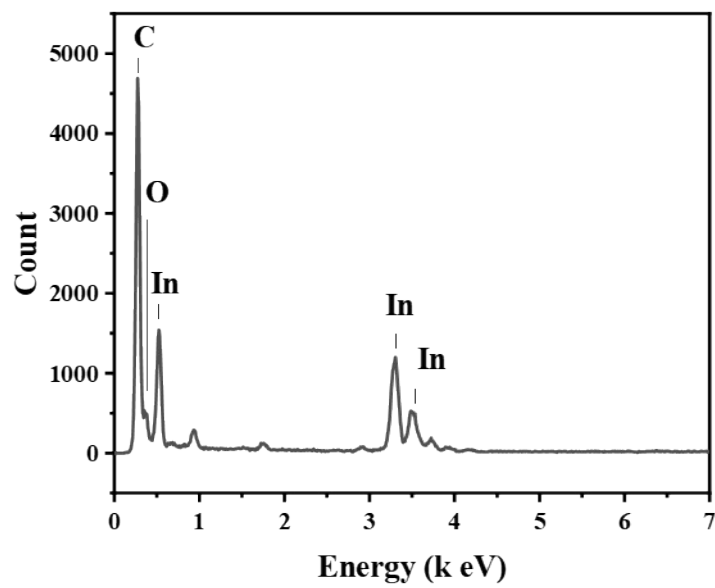


Fig. S7 EDX spectrum of C-In₂O₃.

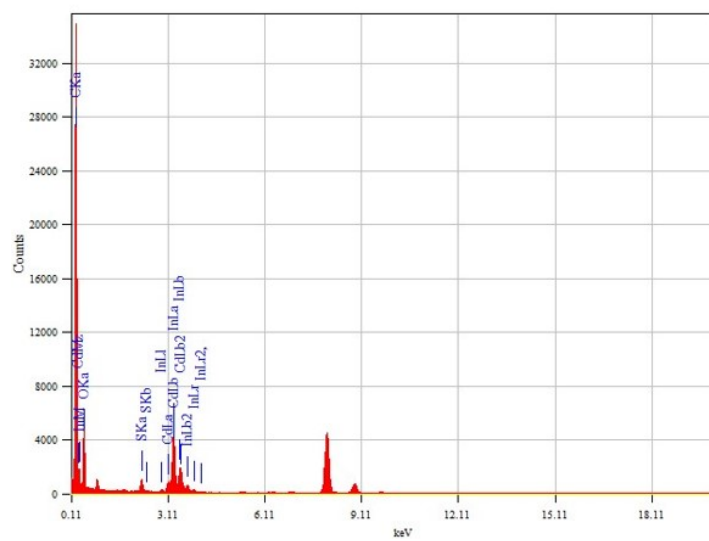


Fig. S8 EDX spectrum of 5CdS/C-In₂O₃.

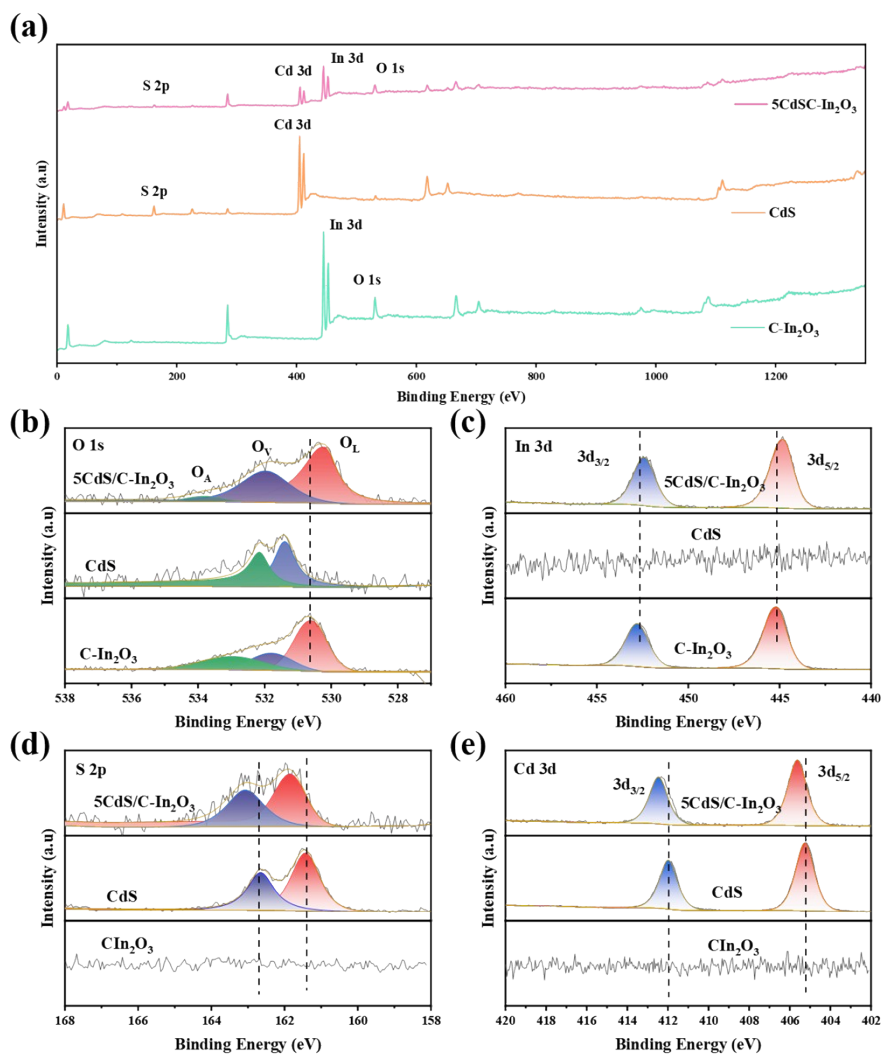


Fig. S9 (a-d) XPS spectra of as-prepared C-In₂O₃, CdS and 5CdS/C-In₂O₃. (a-d) High-resolution XPS spectra of In 3d (a), O 1s (b), Cd 3d (c), S 2p (d) of as-prepared C-In₂O₃, CdS and 5 CdS/C-In₂O₃, respectively.

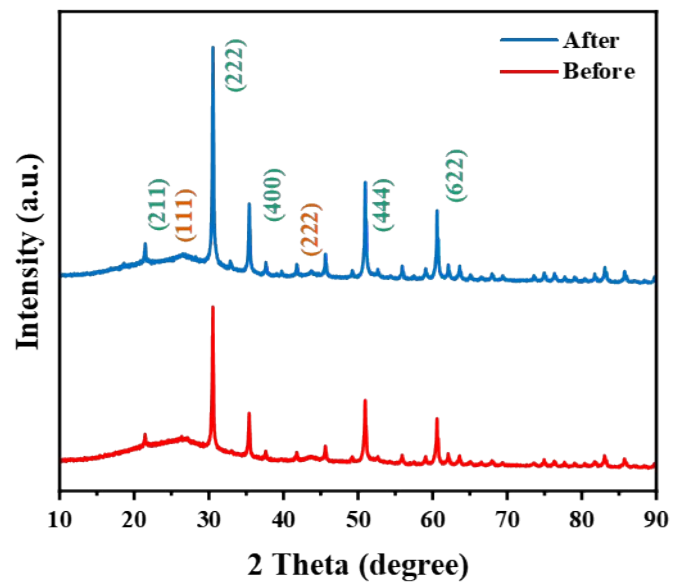


Fig. S10 XRD spectra of 5CdS/C-In₂O₃ after test.

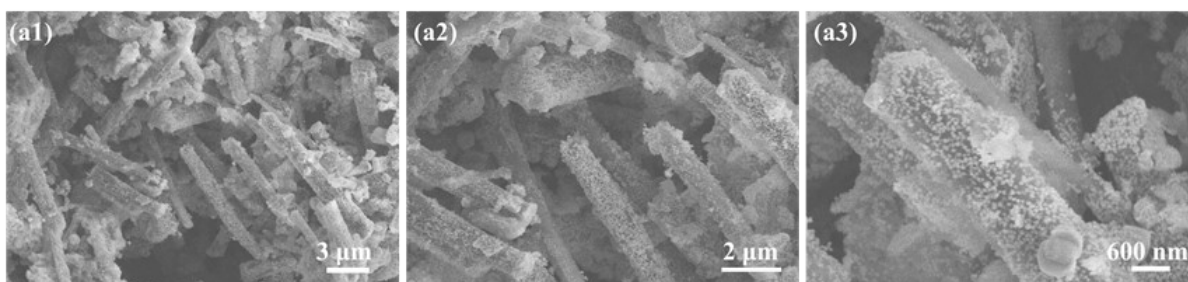


Fig. S11 SEM image of 5CdS/C-In₂O₃ after test.

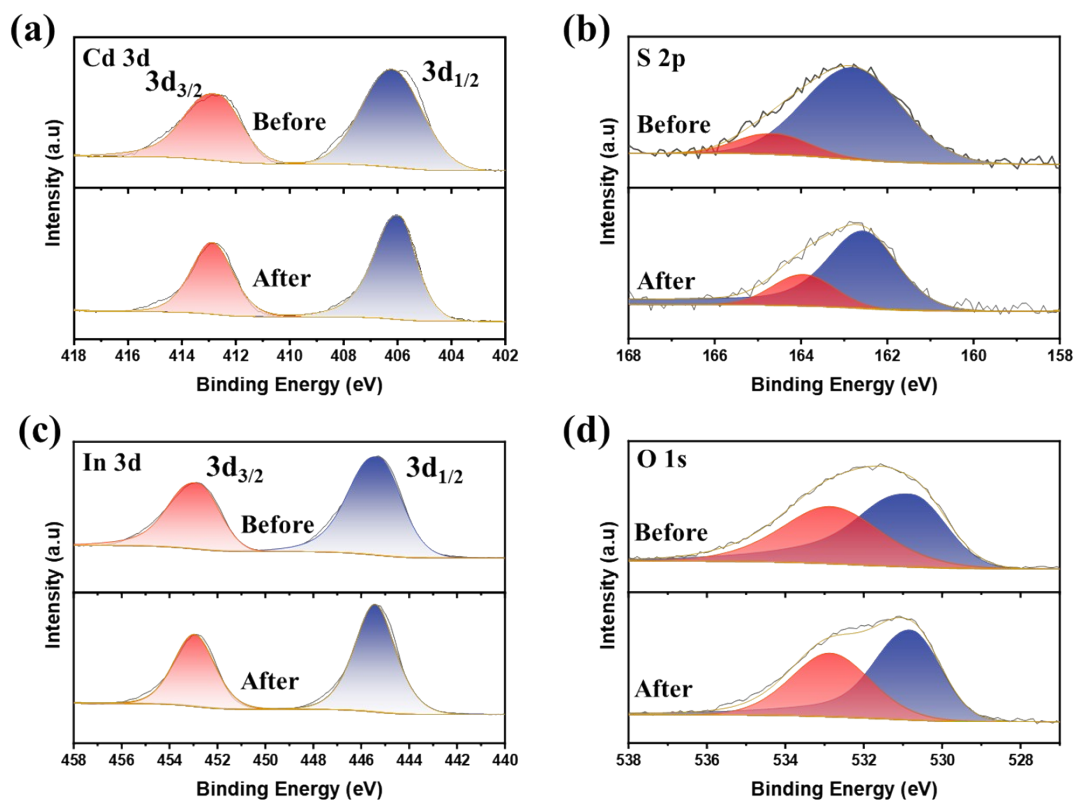


Fig. S12 Comparison of XPS spectra of 5CdS/C-In₂O₃ before and after the reaction. (a-d) High-resolution XPS spectra of Cd 3d (a), S 2p (b), In 3d (c), O 1s (d) of 5 CdS/C-In₂O₃, respectively.

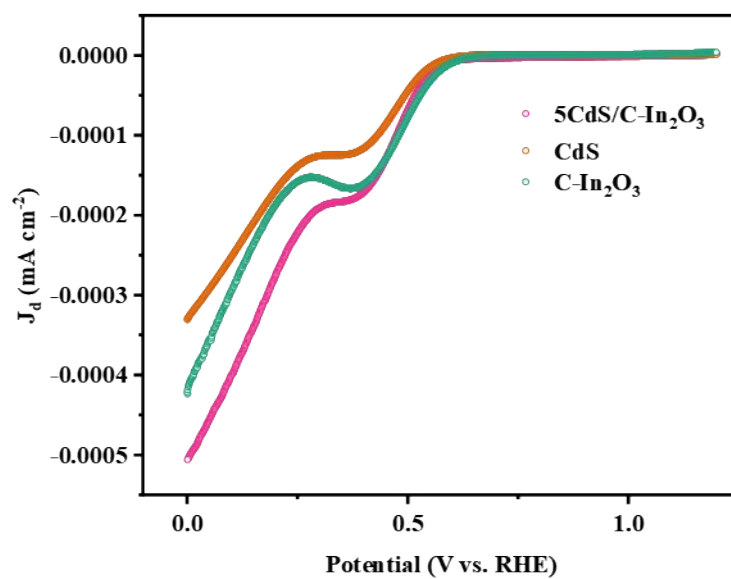


Fig. S13 RRDE polarization curves over C-In₂O₃, CdS and 5CdS/C-In₂O₃ in O₂-saturated 0.1 M KOH (pH = 12.9) at 1600 rpm with ring current (upper part) and density of disk current.

Table S1 experimental details for experimental details for AQY test

wave length (nm)	H ₂ O ₂ yield (mol)	Time (s)	optical power density (W/cm ²)	Area (cm ²)	velocity of light C	Planck constant h	Number of incident photons	H ₂ O ₂ molecules	AQY (%)
400	2.6976 4E-05	3600	0.0126	7.065	300000	6.626E- 34	6.44871 E+20	3.24795E +19	5.036 5994 55
450	2.1944 6E-05	3600	0.0126	7.065	300000	6.626E- 34	7.25479 E+20	2.64213E +19	3.641 9091 8
500	5.5402 8E-06	3600	0.0118	7.065	300000	6.626E- 34	7.54908 E+20	6.6705E+ 18	0.883 6172 24
550	2.3954 3E-06	7200	0.0138	7.065	300000	6.626E- 34	1.94229 E+21	2.88409E +18	0.148 4893 94

Table S2 Comparison of photocatalytic H₂O₂ production rate of CdS/C-In₂O₃ heterostructure with recent reported photocatalysts.

Catalyst	H₂ Evolution ($\mu\text{mol}\cdot\text{g}^{-1}\cdot\text{h}^{-1}$)	Sacrificial agent	Photosensitizer Cocatalyst	Light Source	Ref.
In ₂ S ₃ @In ₂ O ₃	275	\	\	$\lambda \geq 420$ nm	1
In ₂ O ₃ /ZnIn ₂ S ₄	590	\	\	$\lambda \geq 420$ nm	2
In ₂ O ₃ /ZnIn ₂ S ₄	5716	1 mM Na ₂ SO ₃ and Na ₂ S	\	$\lambda \geq 420$ nm	3
Ag-ZnIn ₂ S ₄ /C- In ₂ O ₃	2420	10 vol% isopropanol	\	$\lambda \geq 420$ nm	4
This work	2343	isopropanol	\	$\lambda \geq 420$ nm	

Table S3 τ_1 and τ_2 were fitted with the a biexponential decay model delivered form software and the

average lifetime (τ_a) was obtained using the equation: $\tau_a = \frac{A_1\tau_1^2 + A_2\tau_2^2}{A_1\tau_1 + A_2\tau_2}$.

photocatalyst	τ_1	τ_2	τ_a
C-In ₂ O ₃	1.07	16.45	3.31
CdS	1.60	22.30	4.64
5CdS/C-In ₂ O ₃	1.21	8.57	2.38

References

1. X. Chen, W. Zhang, L. Zhang, L. Feng, C. Zhang, J. Jiang and H. Wang, *ACS Appl. Mater. Interfaces*, 2021, 13, 25868-25878.
2. S. Liu, Y. Mao, Q. Han and X. Liu, *Materials Science in Semiconductor Processing*, 2024, 170, 107978.
3. R. Bariki, K. Das, S. K. Pradhan, B. Prusti and B. G. Mishra, *ACS Appl. Energy Mater.*, 2022, 5, 11002-11017.
4. T. Lei, X. Zhan, Z. Yuan, Z. Wang, H. Yang, D. Zhang, Y. Li, W. Yang, G. Lin and H. Hou, *Sep. Purif. Technol.*, 2025, 359, 130474.